

Claims 1-12 and 14-24 have been finally rejected under 35 U.S.C. 103(a) based on Yamashita in view of Peeters, further in view of Oyama et al. Claim 13 has been finally rejected under 35 U.S.C. 103(a) based on the same combination of references yet further in view of Heller et al.

These rejections are traversed for the following reasons, which lead to the conclusion that considering Yamashita in combination with Peeters and Oyama et al. or further in combination with Heller et al., the presently claimed affinity sensor for detecting specific binding events in response to a sample medium would not have been obvious to one of ordinary skill in the art.

Yamashita discloses a single electron transistor having two conductors mounted on a protein molecule with a quantum dot means positioned therebetween which permits tunneling when the quantum dot means is raised to a required potential.

The Examiner has rejected applicants' prior arguments as "attaching the references individually" and contends that the Oyama reference provides an incentive to combine the three references to arrive at the claimed invention. Applicants respectfully disagree with the Examiner's position.

Again the Examiner mischaracterizes the Yamashita reference as teaching an affinity sensor when it in fact teaches a transistor incorporating protein having a Flavin molecule therein which is switched by raising a potential on a gate

structure. Nothing in this reference suggests that the gate structure and protein with Flavin group can be replaced with the claimed binding pair to produce a tunneling effect.

Reiterating, Yamashita discloses a single electron transistor. A transistor is a controlled turn-on and turn-off switch (as, for instance, illustrated in the Standard Handbook for Electrical Engineers, 11th Edition, 1978, Figure 13-1, copy attached). The transistor disclosed by Yamashita is composed of two electrodes and a means acting as the controlled turn-on and turn-off switch. That transistor is not capable of detecting a binding event in response to a sample medium. Therefore, the transistor disclosed by Yamashita is not a sensor, let alone an affinity sensor for detecting specific binding events in response to a sample medium.

Even if Peeters discloses a microchip having a surface that is formed by a silicon wafer or by a glass target, and detection of other specific binding partners, this, too, does not rectify the fact that Yamashita has no relevance to the present invention.

As seen in the Response to Arguments section of the Office Action, the Examiner relies heavily upon the Oyama et al. teaching to claim there is motivation to combine the references. Even if Oyama et al. discloses a comb electrode structure, this does not rectify the fact that Yamashita has no relevance to the

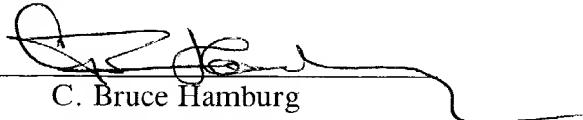
present invention. Oyama discloses a DNA sensor wherein DNA binding with a target molecule disposed on a resonating device, reduces the mass of the target molecule and thereby alters a resonating frequency. This has absolutely nothing to do with binding pairs enabling electron tunneling. Yamashita only effects tunneling when a gate voltage is applied. Nothing suggests that the combining of a binding pair would provide for tunneling. Also, nothing in the references would provide one with a reasonable expectation of success in building a sensor as claimed wherein the combination of the binding pair effects tunneling.

Likewise, Heller cannot rectify that Yamashita has no relevance to the present invention.

Applicant respectfully requests a three month extension of time for responding to the Office Action. Please charge the fee of \$465.00 for the extension of time to Deposit Account No. 10-1250. A Notice of Appeal accompanies this response.

Respectfully submitted,

JORDAN AND HAMBURG LLP

By 

C. Bruce Hamburg

Reg. No. 22,389

Attorney for Applicants

Jordan and Hamburg LLP
122 East 42nd Street
New York, New York 10168
(212) 986-2340

APPENDIX I**AMENDED CLAIMS WITH AMENDMENTS INDICATED THEREIN
BY BRACKETS AND UNDERLINING**

1. (Thrice Amended) Affinity sensor for detecting specific binding events in response to a sample medium, comprising a carrier substrate provided with at least two electrodes and having a predetermined area, said electrodes being equidistantly spaced apart from each other and engagingly bordering said area on opposing sides, at least said area being adapted for receiving immobilized specific binding partners for coupling complementarily associated binding partners directly or via further specific binding molecules, said area being accessible to said complementarily associated binding partners provided in a sample medium and having a minimum width adapted for capture of at least one of said complementarily associated binding partners provided with one electrically conductive particle within said area in such a way as to allow for formation of a respective tunnel contact junction between the particle and the electrodes.

Institute of Physics • American Institute of Physics Handbook

Boussinesq • Metric Standard Handbook for Mechanical Engineers

Bureau of Industrial Power Systems Handbook

Gandy and Glazier • Materials Handbook

Guggenheim • Handbook of Mathematical Tables and Formulas

Hannay and Alny • Handbook of Probability and Statistics with Tables

Cordón and Okohaus • Handbook of Physics

Conditte • Energy Technology Handbook

Crombie • Basic Electronic Instrument Handbook

Crone • Crystal Circuits Handbook

Croft, Curr, and Watt • American Electronics' Handbook

Dietrich Gross, Inc., The • Automatic Data Processing Handbook

Fink • Electronics Engineer's Handbook

Grainger • Engineering Formulas

Graw-Horn • Handbook of Telemetry and Remote Control

Hemmer • Communications System Engineering Handbook

Herper • Handbook of Components for Electronics

Herper • Handbook of Electronic Packaging

Herper • Handbook of Materials and Processes for Electronics

Herper • Handbook of Thick Film Hybrid Microelectronics

Herper • Handbook of Wirebonding, Casting, and Interconnecting for Electronics

Honey • Radio Engineering Handbook

Hicks • Standard Handbook of Engineering Calculations

Hunter • Handbook of Semiconductor Electronics

Hyman • Reliability Handbook

Jusk • Antenna Engineering Handbook

Koren • Quality Control Handbook

Kaufman and Sisonson • Handbook for Electronic Engineering Technicians

Korn and Korn • Mathematical Handbook for Scientists and Engineers

Krebs • The Engineer's and Carpenter's Handbook

Landolt • System Engineering Handbook

Wolcott and Goss • Handbook of Thin Film Technology

Markin • Electronics Dictionary

Mashov • Handbook of Electrical Control Circuits

Matthew Jellie-Cleaff • Handbook of Industrial and Electrotechnical Circuits

McCormick • Handbook of the National Electrical Code

Perry • Engineering Manual

Schotek • Radar Handbook

Sigerson • Motor Applications and Maintenance Handbook

Stearns • Switchgear and Control Handbook

Street and Stognum • Handbook of Operational Amplifier Circuit Design

Tread • Control Engineers' Handbook

Tunnu • Engineering Mathematics Handbook

Tunno • Handbook of Physical Calculations

Tunno • Technology Mathematics Handbook

Handbook for Engineers

DONALD G. FINK *Editor-in-Chief*

General Manager and Executive Director, Raytheon, Institute of
Electrical and Electronics Engineers; formerly Vice President—
Research, Philco Corporation; President of the Institute of
Radio Engineers; Editor of the *Proceedings of the IEEE*; Fellow
of the IEEE; Fellow of the IRE Standard;
Fellow Member, Phi Kappa Phi; Member of the
National Academy of Engineering.

H. WAYNE BEATTY *Associate Editor*

Senior Editor, *Electrical World*; Member of the Institute
of Electrical and Electronics Engineers and of the IEEE Power
Engineering Society; Transmission
and Distribution Committee.



Eleventh Edition

McGRAW-HILL BOOK COMPANY

New York St. Louis San Francisco Auckland Bogotá

Sydney Ahmedabad London Madrid

Mexico Mexico New Delhi Panama

Perth São Paulo Singapore

Sydney Tokyo Toronto

The Library of Congress cataloged the First Issue as follows:

Stanford handbook for electrical engineers. 1st ed.

11 diag., tables. 15x24 cm.

Editors: A. B. Sch. F. F. Foulke.—Ills.

A. E. Konarzynski

1. Electric engineering—Handbooks, manuals, etc.

I. Foulke, Frank Fuller, 1877- ed. II. Konarzynski, Archer Eben, 1885- ed.

TK51.31

565564

Library of Congress

[550.19]

ISBN 0-07-056564-X

Contents

Preface to the Elementary Edition &
Introduction to the Advanced Edition

Section 1. Quantities, Units, Symbols, Constants, and Conversion Factors 1-1
SI units and conversion factors; prefixes and usage; definitions of quantities:
letter and graphic symbols; physical constants and numerical values

Section 2. Electric and Magnetic Circuits 2-1
Actions and reactions of charge; potential; current; electric and magnetic fields;
in circuits; forces; losses; steady-state and transient effects; filter design by
insertion loss method

Section 3. Measurements and Instruments 3-1
Principles and equipment for measuring electric, magnetic, mechanical,
thermal, and other meteorologic quantities; electricity; measurement errors

11-1557000 KKF 7005-20109

Section 4. Properties of Materials 4-1
Conductors; magnetic materials; insulating materials; structural materials

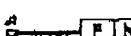
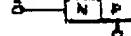
Section 5. Steam Power Plants 5-1
Fossil-fueled steam generation; nuclear-fueled steam generation; nuclear
power for the future; circulating water systems and components

Section 6. Prime Movers 6-1
Steam engines and turbines; steam turbine applications; steam turbine
performance; control and protective systems; lubrication and hydraulic
systems; gas turbines

The McGraw-Hill editors for this book were Horace R. Crawford and
Joseph Williams; the designer was Herman Auscheck; and the production
supervisor was Frank Rabinowitz. It was set in Goudy Old Style
by Baskerville Graphics, Inc.

Printed and bound by The Kingstone Press

Section 1. Alternating-Current Generators 1-1
Magnetic circuits; field and armature designs; insulation; cooling; mechanical
construction; transient effects; losses and efficiencies; test methods

Device name	Structure	Symbol	V-I characteristic	Principal use
Conventional diode				Rectifier
Avalanche diode				Rectifier
Thyristor				Controlled turn-on switch
Triac				Bidirectional controlled turn-on switch
Transistor				Controlled turn-on and turn-off switch

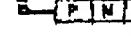
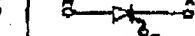
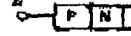
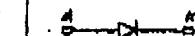
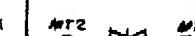
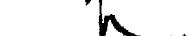
Gate-controlled switch				Controlled turn-on and turn-off
Shockley diode (RSAT)				High i_c/v_d breaker switch
Zener diode				Voltage reference
Trigger diode (stern)				Trigger device to initiate thyristor or triac turn-on

Fig. 10-1. Devices commonly used in power circuits.